





HIGH EFFICIENCY CLASS-G ADSL LINE DRIVER

FEATURES

- Low Total Power Consumption Increases ADSL Line Card Density (20 dBm on Line)
 - 600 mW w/Active Termination (Full Bias)
 - 530 mW w/Active Termination (Low Bias)
- Low MTPR of -74 dBc (All Bias Conditions)
- High Output Current of 500 mA (typ)
- Wide Supply Voltage Range of ±5 V to ±15 V [V_{CC(H)}] and ±3.3 V to ±15 V [V_{CC(L)}]
- Wide Output Voltage Swing of 43 Vpp Into 100-Ω Differential Load [V_{CC(H)} = ±12 V]
- Multiple Bias Modes Allow Low Quiescent Power Consumption for Short Line Lengths
 - 160-mW/ch Full Bias Mode
 - 135-mW/ch Mid Bias Mode
 - 110-mW/ch Low Bias Mode
 - 75-mW/ch Terminate Only Mode
 - 13-mW/ch Shutdown Mode
- Low Noise for Increased Receiver Sensitivity
 - 3.3 pA/√Hz Noninverting Current Noise
 - 9.5 pA/√Hz Inverting Current Noise
 - 3.5 nV/√Hz Voltage Noise

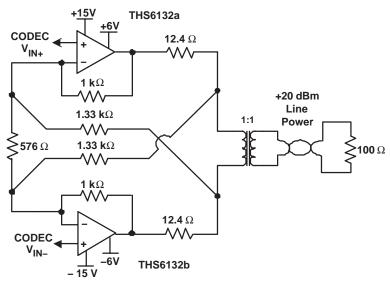
APPLICATIONS

 Ideal for Active Termination Full Rate ADSL DMT applications (20-dBm Line Power)

DESCRIPTION

The THS6132 is a Class-G current feedback differential line driver ideal for full rate ADSL DMT systems. Its extremely low power consumption of 600 mW or lower is ideal for ADSL systems that must achieve high densities in ADSL central office rack applications. The unique patent pending architecture of the THS6132 allows the quiescent current to be much lower than existing line drivers while still achieving very high linearity. In addition, the multiple bias settings of the amplifiers allow for even lower power consumption for line lengths where the full performance of the amplifier is not required. The output voltage swing has been vastly improved over first generation Glass-G amplifiers and allows the use of lower power supply voltages that help conserve power. For maximum flexibility, the THS6132 can be configured in classical Class-AB mode requiring only as few as one power supply.

Typical ADSL CO Line Driver Circuit Utilizing Active Impedance Supporting A 6.3 Crest Factor



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Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage.

ORDERING INFORMATION

PRODUCT	PACKAGE	PACKAGE CODE	SYMBOL	TA	ORDER NUMBER	TRANSPORT MEDIA
TUCC420\/ED	TOED SO Davis DADIM	VED 00	TI 100422		THS6132VFP	Tube
THS6132VFP	TQFP-32 PowerPAD™	VFP-32	THS6132	-40°C to 85°C	THS6132VFPR	Tape and reel
THS6132RGW	Leadless 25-pin 5,mm x 5, mm PowerPAD™	RGW-25	6132	-40 0 10 05 0	THS6132RGWR	Tape and reel

PACKAGE DISSIPATION RATINGS

PACKAGE	ΘЈА	ΘJC	$T_A \le 25^{\circ}C$ POWER RATING(1)	T _A = 70°C POWER RATING(1)	T _A = 85°C POWER RATING ⁽¹⁾
VFP-32	29.4°C/W	0.96°C/W	3.57 W	2.04 W	1.53 W
RGW-25	31°C/W	1.7°C/W	3.39 W	1.94 W	1.45 W

⁽¹⁾ Power rating is determined with a junction temperature of 130°C. This is the point where distortion starts to substantially increase. Thermal management of the final PCB should strive to keep the junction temperature at or below 125°C for best performance.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted(1)

		THS6132
Supply voltage	e, V _{CC(H)} and V _{CC(L)} (2)	±16.5 V
Input voltage, \	V _I	±VCC(L)
Output current	, I _O (3)	900 mA
Differential inp	ut voltage, V _{IO}	±2 V
Maximum junc	tion temperature, T _J (see Dissipation Rating Table for more information)	150°C
Operating free	-air temperature, T _A	-40°C to 85°C
Storage tempe	rature, T _{Stg}	65°C to 150°C
Lead temperat	ure, 1,6 mm (1/16-inch) from case for 10 seconds	300°C
	НВМ	1 kV
ESD ratings	CDM	500 V
	MM	200 V

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

⁽²⁾ $V_{CC(H)}$ must always be greater than or equal to $V_{CC(L)}$ for proper operation. Class-AB mode operation occurs when $V_{CC(H)}$ is equal to $V_{CC(L)}$ and is considered acceptable operation for the THS6132 even though it is not fully specified in this mode of operation.

⁽³⁾ The THS6132 incorporates a PowerPAD on the underside of the chip. This acts as a heatsink and must be connected to a thermally dissipating plane for proper power dissipation. Failure to do so may result in exceeding the maximum junction temperature that could permanently damage the device. See TI Technical Brief SLMA002 for more information about utilizing the PowerPAD thermally enhanced package.



RECOMMENDED OPERATING CONDITIONS

		MIN	NOM	MAX	UNIT
Committee	+VCC(H) to -VCC(H)	±V _{CC(L)}	±15	±16	.,
Supply voltage	+VCC(L) to $-VCC(L)$	±3.3	±5	±V _{CC(H)}	V
Operating free-air	temperature, T _A	-40		85	°C

ELECTRICAL CHARACTERISTICS

over recommended operating free-air temperature range, $T_A = 25^{\circ}C$, $V_{CC(H)} = \pm 15$ V, $V_{CC(L)} = \pm 5$ V $R_F = 1.5$ k Ω , Gain = +10, Full Bias Mode, $R_L = 50$ Ω (unless otherwise noted)

	PARAMETE	R	TES	T CONDITIONS	MIN	TYP	MAX	UNIT
	Multitone power ratio)	Gain =+11, 163kHz +20 dBm Line Powe active termination, s	r, 1:1.1 transformer,		-74		dBc
	Receive band spill-o	ver	Gain =+11, 25 kHz t applied	o 138 kHz with MTPR signal		-95		dBc
				Differential load = 100 Ω		-84		dBc
HD	Harmonic distortion	,	2 nd harmonic	Differential load = 25 Ω		-69		UBC
пи	Configuration, $f = 1 \text{ MHz}$, $V_O(PP) = 2 \text{ V}$, $Gain = +10$)		3rd harmonic	Differential load = 100 Ω		-92		dBc
	*O(FF) = 2 *, Gain	- 110)	3 rd narmonic	Differential load = 25 Ω		-73		ubc
Vn	Input voltage noise		f = 10 kHz			3.5		nV/√Hz
	Input current noise +Input		f = 10 kHz			3.3		pA/√Hz
In	input current noise	-Input	1 = 10 KHZ			9.5		pA/\nz
	Crosstalk		f = 1 MHz, $R_L = 100 \Omega,$	$V_{O(PP)} = 2 V$, Gain = +2		-52		dBc
OUTP	UT CHARACTERIS	TICS	•					•
			V	R _L = 100 Ω	±10.4	±10.8		V
\/-	Cinala andad autou	t valtaga avring	$V_{CC(H)} = \pm 12 \text{ V}$	$R_L = 30 \Omega$	±9.9	±10.4		V
VO	Single-ended output	t voltage swing	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	R _L = 100 Ω	±13.3	±13.8		V
			$V_{CC(H)} = \pm 15 \text{ V}$	$R_L = 50 \Omega$	±13	±13.6		V
	Output voltage trans	ition from V _{CC(L)} to	R _I = 50 Ω	$V_{CC(L)} = \pm 5 \text{ V}$		±3.1		V
	V _{CC(H)} (Point wher	e ICC(L) = ICC(H)	KL = 50 22	$V_{CC(L)} = \pm 6 \text{ V}$		±3.9		V
l.	Output current (1)		R _I = 10 Ω	$V_{CC(H)} = \pm 12 \text{ V}$		±500		mA
10	·		KL = 10 22	$V_{CC(H)} = \pm 15 \text{ V}$	±400	±500		IIIA
I(SC)	Short-circuit current	(1)	$R_L = 1 \Omega$	$V_{CC(H)} = \pm 15 \text{ V}$		±750		mA
	Output resistance		Open-loop			5		Ω
	Output resistance—	terminate mode	f = 1 MHz,	Gain = +10		0.35		Ω
	Output resistance—	shutdown mode	f = 1 MHz,	Open-loop		5.5		kΩ

⁽¹⁾ A heatsink is required to keep the junction temperature below absolute maximum rating when an output is heavily loaded or shorted. See Absolute Maximum Ratings section for more information.



ELECTRICAL CHARACTERISTICS (continued)

over recommended operating free-air temperature range, $T_A = 25^{\circ}C$, $V_{CC(H)} = \pm 15$ V, $V_{CC(L)} = \pm 5$ V RF = 1.5 k Ω , Gain = +10, Full Bias Mode, $R_L = 50 \Omega$ (unless otherwise noted)

POWER	R SUPPLY							
	PARAMETER	TES'	T CONDITIONS	MIN	TYP	MAX	UNIT	
Voor	Operating range	±V _{CC(H)}	±VCC(L)	±15	±16.5	V		
VCC(x)	Operating range	±V _{CC(L)}		±3	±5	±VCC(H)	V	
		$V_{CC(L)} = \pm 5 \text{ V};$	$T_A = 25^{\circ}C$	5.7	6.4	7.5	mA	
	Quiescent current (each driver) Full-bias mode (Bias-1 = 1, Bias-2 = 1, Bias-3 = X) (Icc trimmed with V _{CC} (H) = ±15 V, V _{CC} (L) = ±5 V)	(V _{CC(H)} =±15 V)	T _A = full range			8.1	ША	
		$V_{CC(L)} = \pm 6 \text{ V};$	T _A = 25°C		6.7		mA	
		$(V_{CC(H)} = \pm 15 \text{ V})$	T _A = full range				ША	
		$V_{CC(H)} = \pm 12 \text{ V};$	T _A = 25°C		3.1		mA	
		$(V_{CC(L)} = \pm 5 \text{ V})$	T _A = full range				ША	
		$V_{CC(H)} = \pm 15 \text{ V};$	$T_A = 25^{\circ}C$	2.9	3.25	3.75	mA	
1		$(V_{CC(L)} = \pm 5 \text{ V})$	T _A = full range			4.25		
ICC		Mid; Bias $-1 = 1$, Bias $-2 = 0$, Bias $-3 = 1$		5.0	5.6	6.8	mA	
	Quiescent current (each driver) Variable bias modes,	Low; Bias-1 = 1, Bias-2 = 0, Bias-3 = 0		4.25	4.8	6.0		
	$V_{CC(L)} = \pm 5 \text{ V}$	Terminate; Bias-1 = 0, Bias-2 = 1, Bias-3 = $X(1)$		3.2	3.8	4.5		
		Shutdown; Bias-1 =	Shutdown; Bias-1 = 0, Bias-2 = 0, Bias-3 = $X^{(1)}$		1	1.3		
		Mid; Bias-1 = 1, Bias	:–2 = 0, Bias–3 = 1	2.4	2.7	3.0		
	Quiescent current (each driver) Variable bias modes,	Low; Bias-1 = 1, Bia	is-2 = 0, Bias-3 = 0	1.9	2.15	2.4	A	
	$V_{CC(H)} = \pm 15 \text{ V}$	Terminate; Bias-1 =	0, Bias-2 = 1, Bias-3 = X(1)	1.1	1.3	1.5	mA	
		Shutdown; Bias-1 =	0, Bias-2 = 0, Bias-3 = X(1)		0.1	0.5		
		Vaan IEV	T _A = 25°C	-70	-82			
DCDD	Power supply rejection ratio	$V_{CC(L)} = \pm 5V$	T _A = full range	-68			dB	
PSRR	$(\Delta V_{CC(x)} = \pm 1 \text{ V})$	V	T _A = 25°C	-70	-82			
	• •	$V_{CC(H)} = \pm 15V$	T _A = full range	-68				

⁽¹⁾ X is used to denote a logic state of either 1 or 0.



ELECTRICAL CHARACTERISTICS (continued) over recommended operating free-air temperature range, $T_A = 25^{\circ}C$, $V_{CC(H)} = \pm 15$ V, $V_{CC(L)} = \pm 5$ V RF = 1.5 kΩ, Gain = +10, Full Bias Mode, $R_L = 50$ Ω (unless otherwise noted)

DYNAMIC PERFORMANCE								
	PARAMETER	TES	T CONDITIONS	MIN	TYP	MAX	UNIT	
			Gain = +1, RF = 750 Ω		80			
		D. 100 O	Gain = +2, RF = 620 Ω		70		MHz	
		$R_L = 100 \Omega$	Gain = +5, RF = 500Ω		60] IVITZ	
DIM	Single-ended small-signal bandwidth		Gain = +10, RF = 1 k Ω	20]		
BW	$(-3 \text{ dB}), V_0 = 0.1 \text{ Vrms}$		Gain = +1, RF = 750 Ω		60			
		D 05.0	Gain = +2, RF = 620 Ω		55		MHz	
		$R_L = 25 \Omega$	Gain = +5, RF = 500Ω		50		IVITZ	
			Gain = +10, RF = 1 k Ω		17			
SR	Single-ended slew-rate(1)	V _O = 20 V _{PP} ,	Gain =+10		300		V/μs	

⁽¹⁾ Slew-rate is defined from the 25% to the 75% output levels

DC PE	RFORMANCE						
	PARAMETER	TEST C	ONDITIONS	MIN	TYP	MAX	UNIT
	lanut effect voltage		T _A = 25°C		1	15	
	Input offset voltage		T _A = full range			20	\/
V_{OS}	Differential effect values	$V_{CC(L)} = \pm 5 \text{ V}, \pm 6 \text{ V}$	T _A = 25°C	0.3	6	mV	
	Differential offset voltage		T _A = full range			8	
	Offset drift		T _A = full range		40		μV/°C
	land him and		T _A = 25°C		1	15	
	-Input bias current		T _A = full range			20	
IB	. Land bin comment	$V_{CC(L)} = \pm 5 \text{ V}, \pm 6 \text{ V}$	T _A = 25°C		1.5	15	μΑ
	+ Input bias current		T _A = full range			20	
Z _{OL}	Open loop transimpedance	$R_L = 1 k\Omega$			2		ΜΩ



ELECTRICAL CHARACTERISTICS (continued)

over recommended operating free-air temperature range, T_A = 25°C, $V_{CC(H)}$ = ±15 V, $V_{CC(L)}$ = ±5 V R_F = 1.5 k Ω , Gain = +10, Full Bias Mode, R_L = 50 Ω (unless otherwise noted)

INPUT	INPUT CHARACTERISTICS								
	PARAMETER	TEST C	ONDITIONS	MIN	TYP	MAX	UNIT		
			T _A = 25°C	±2.7	±3.0				
V _{ICR} I	Input common-mode voltage range(1)	$V_{CC(L)} = \pm 5 \text{ V}$	T _A = full range	±2.6			V		
		$V_{CC(L)} = \pm 6 \text{ V}$	T _A = 25°C		±4.0				
	REF pin input voltage range	V _{CC} -(L)= ±5 V			±2.5		V		
	REF pili iriput voltage range	$VCC(L) = \pm 6 V$			±3.5		V		
CMDD	Common-mode rejection ratio	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	$T_A = 25^{\circ}C$	60	67		dB		
CMRR	Common-mode rejection ratio	$V_{CC(L)} = \pm 5 \text{ V}, \pm 6 \text{ V}$	T _A = full range	57			uБ		
_	Innut registance	+ Input			800		kΩ		
R _I	Input resistance	- Input	_		45	·	Ω		
C _I	Differential Input capacitance				1.2		pF		

⁽¹⁾ To conserve as much power as possible, the input stage of the THS6132 is powered from the $V_{CC(L)}$ supplies and is limited by the $V_{CC(L)}$ supply voltage. For Class-AB operation, connect the $V_{CC(L)}$ supplies to $V_{CC(H)}$.

LOGIC CONTROL CHARACTERISTICS							
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
VIH	Bias pin voltage for logic 1	Relative to DGND pin voltage	2.0			V	
VIL	Bias pin voltage for logic 0	Relative to DGND pin voltage			0.8	V	
lн	Bias pin current for logic 1	V _{IH} = 5 V, DGND = 0 V		-0.1	-0.2	μΑ	
I _L	Bias pin current for logic 0	V _{IL} = 0 V, DGND = 0 V		-0.1	-0.2	μΑ	
	Transition time—logic 0 to logic 1 ⁽¹⁾			0.1		μs	
	Transition time—logic 1 to logic 0 ⁽¹⁾			0.2		μs	
	DGND useable range		-VCC(H)		+VCC(H) -5	V	

⁽¹⁾ Transition time is defined as the time from when the logic signal is applied to the time when the supply current has reached half its final value.

LOGIC	LOGIC TABLE								
BIAS-1 BIAS-2 BIAS-3 FUNCTION DESCRIPTION									
1	1	χ(1)	Full bias mode	Amplifiers ON with lowest distortion possible					
1	0	1	Mid bias mode	Amplifiers ON with power savings with a reduction in distortion performance					
1	0	0	Low bias mode	Amplifiers ON with enhanced power savings and a reduction of distortion performance					
0	1	χ(1)	Terminate mode	Lowest power state with +Vin pins internally connect to REF pin and output has low impedance					
0	0	χ(1)	Shutdown mode	Amplifiers OFF and output has high impedance					

⁽¹⁾ X is used to denote a logic state of either 1 or 0.

NOTE: The default state for all logic pins is a logic one (1).



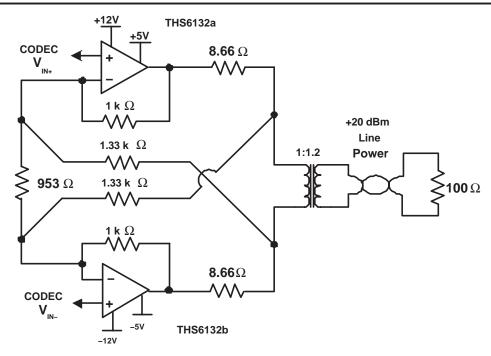
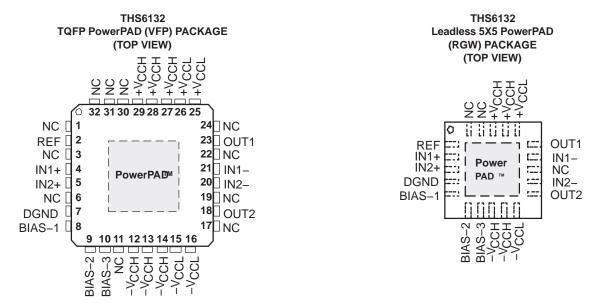


Figure 1. ±12 V Active Termination ADSL CO Line Driver Circuit (Synthesis Factor = 4; CF = 5.6)

PIN ASSIGNMENTS



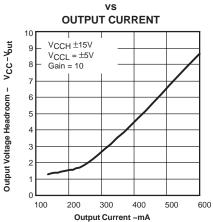


TYPICAL CHARACTERISTICS

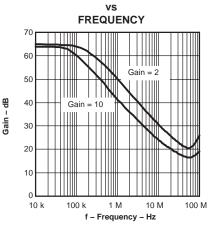
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OUTPUT VOLTAGE HEADROOM



COMMON-MODE REJECTION RATIO



CROSSTALK

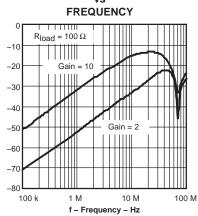
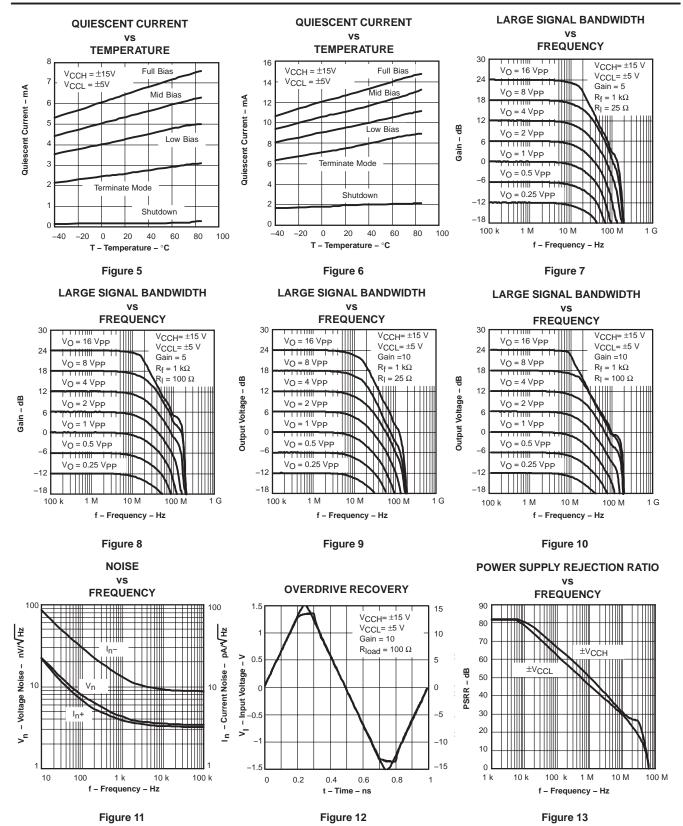


Figure 2

Figure 3

Figure 4







SMALL SIGNAL FREQUENCY RESPONSE

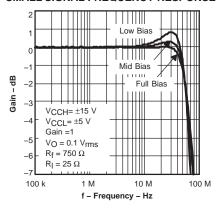


Figure 14

SMALL SIGNAL FREQUENCY RESPONSE SMALL SIGNAL FREQUENCY RESPONSE

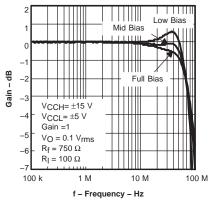


Figure 15

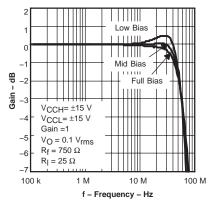


Figure 16
SMALL SIGNAL BANDWIDTH

SMALL SIGNAL BANDWIDTH

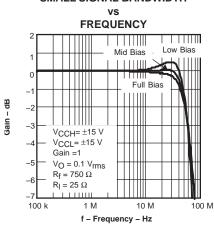


Figure 17

SMALL SIGNAL BANDWIDTH

vs

FREQUENCY

8

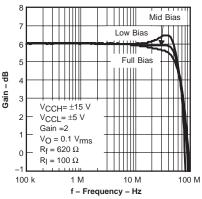


Figure 18

VS
FREQUENCY

8
7
6
5
5
Full Bias

VCCH= ±15 V
VCCL= ±15 V
VCCL= ±15 V
Gain = 2
VO = 0.1 V_{rms}
0
R_f = 620 Ω
R_l = 25 Ω
1
100 k
1 M
10 M
10 M
10 M

Figure 19

f - Frequency - Hz

SMALL SIGNAL BANDWIDTH

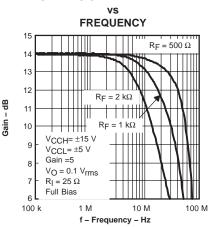


Figure 20

SMALL SIGNAL BANDWIDTH

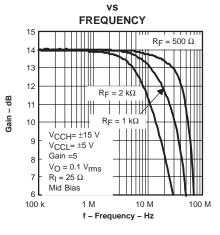


Figure 21

SMALL SIGNAL BANDWIDTH

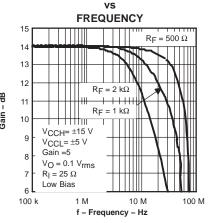
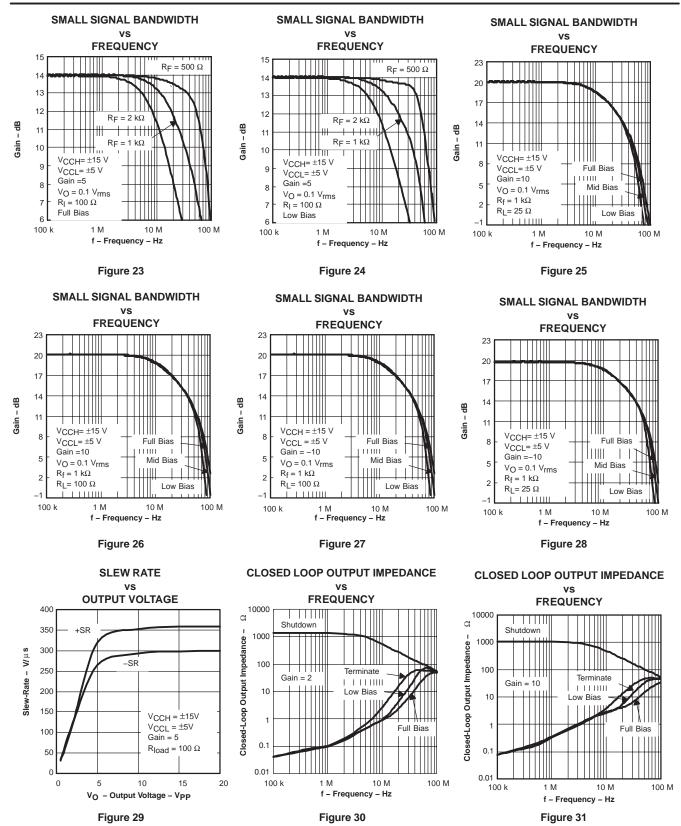
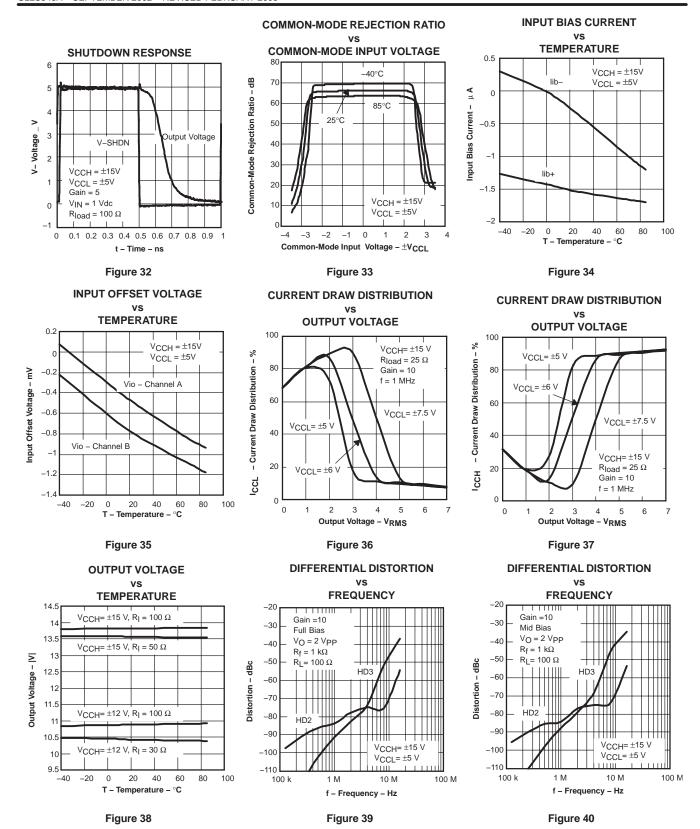


Figure 22

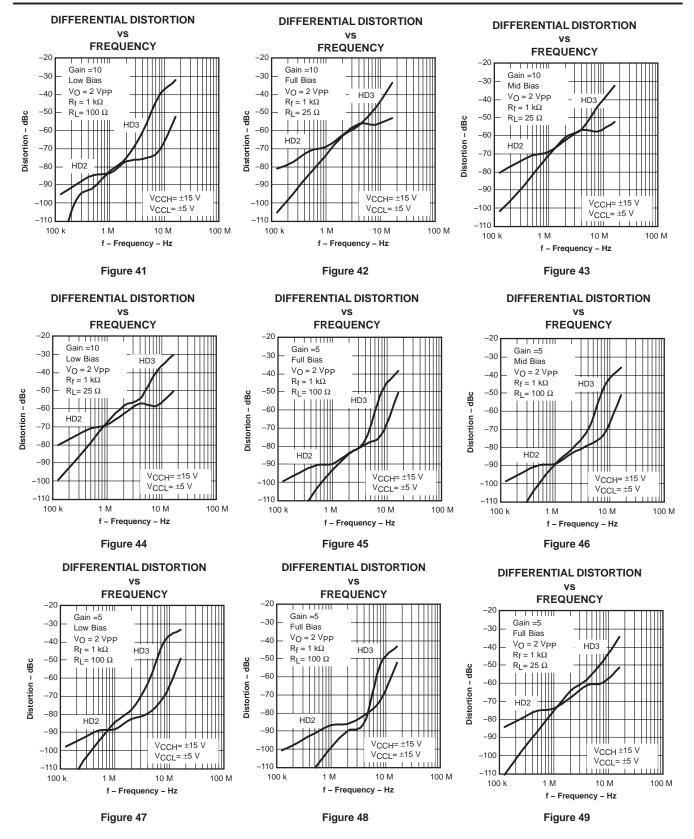




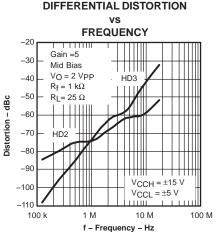












FREQUENCY -20 Gain =5 -30 Low Bias V_O = 2 V_{PP} HD3 -40 $R_f = 1 k\Omega$ -50 R_L= 25 Ω -60 -70 HD2 -80 -90 V_{CCH} = ±15 V -100 V_{CCL} = ±5 V -110 100 k 10 M 100 M f - Frequency - Hz

DIFFERENTIAL DISTORTION

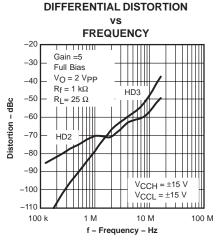
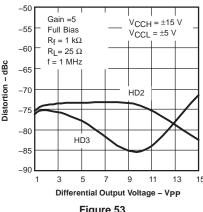


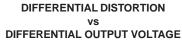
Figure 50

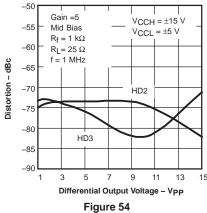
Figure 51

Figure 52

DIFFERENTIAL DISTORTION vs **DIFFERENTIAL OUTPUT VOLTAGE**







DIFFERENTIAL DISTORTION vs

DIFFERENTIAL OUTPUT VOLTAGE

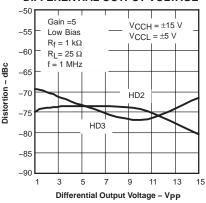


Figure 53

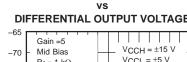
DIFFERENTIAL DISTORTION

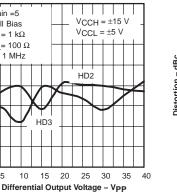
DIFFERENTIAL OUTPUT VOLTAGE

HD₂

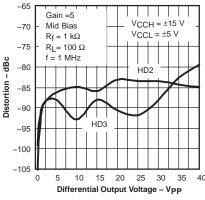
25

DIFFERENTIAL DISTORTION





DIFFERENTIAL OUTPUT VOLTAGE



DIFFERENTIAL DISTORTION VS **DIFFERENTIAL OUTPUT VOLTAGE**

Figure 55

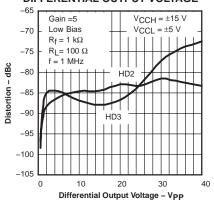


Figure 56

15 20

HD3

Figure 57

Figure 58

-65

-70

-75

-80

-85

-90

-95

-100

-105

Distortion – dBc

Gain =5

Full Bias

 $R_f = 1 k\Omega$

R_L= 100 Ω

f = 1 MHz

DIFFERENTIAL DISTORTION



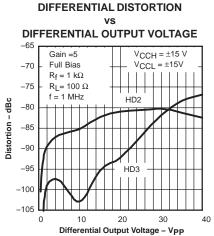


Figure 59

DIFFERENTIAL OUTPUT VOLTAGE -50 Gain =10 V_{CCL} = ±15 V V_{CCL} = ±5V Full Bias -55 $R_f = 1 k\Omega$ -60 R_L= 25 Ω f = 1 MHz HD2 -65 Distortion -70 -75 -80 HD3 -85 -90 11 13 15 Differential Output Voltage - Vpp

DIFFERENTIAL DISTORTION

Figure 60

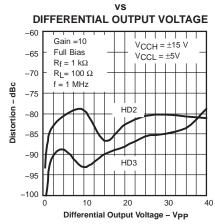
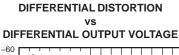


Figure 61



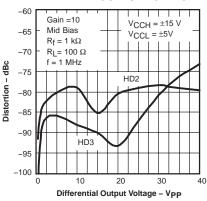


Figure 62

DIFFERENTIAL DISTORTION vs DIFFERENTIAL OUTPUT VOLTAGE

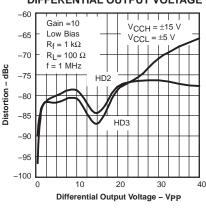


Figure 63

SINGLE ENDED DISTORTION vs FREQUENCY

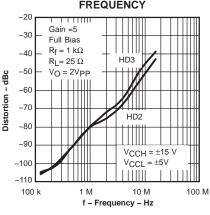


Figure 64

SINGLE ENDED DISTORTION

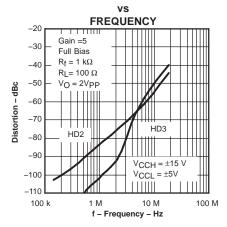


Figure 65

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)	
						(4)	(5)			
THS6132VFP	Active	Production	HLQFP (VFP) 32	250 JEDEC TRAY (5+1)	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	THS6132	
THS6132VFP.A	Active	Production	HLQFP (VFP) 32	250 JEDEC TRAY (5+1)	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	THS6132	

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



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TRAY

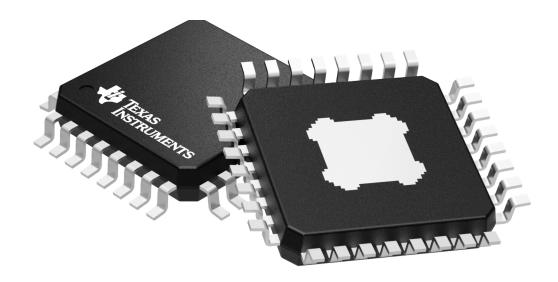


Chamfer on Tray corner indicates Pin 1 orientation of packed units.

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	Unit array matrix	Max temperature (°C)	L (mm)	W (mm)	Κ0 (μm)	P1 (mm)	CL (mm)	CW (mm)
THS6132VFP	VFP	HLQFP	32	250	10 x 25	150	315	135.9	7620	12.2	11.1	11.25
THS6132VFP.A	VFP	HLQFP	32	250	10 x 25	150	315	135.9	7620	12.2	11.1	11.25

PLASTIC QUAD FLATPACK



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4200791/D



VFP (S-PQFP-G32)

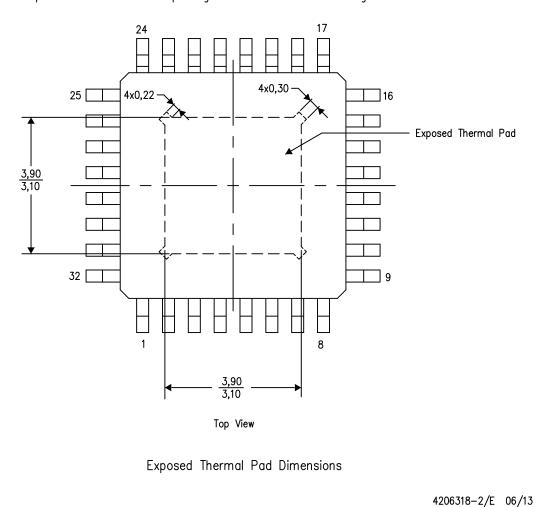
PowerPAD™ PLASTIC QUAD FLATPACK

THERMAL INFORMATION

This PowerPAD ™ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

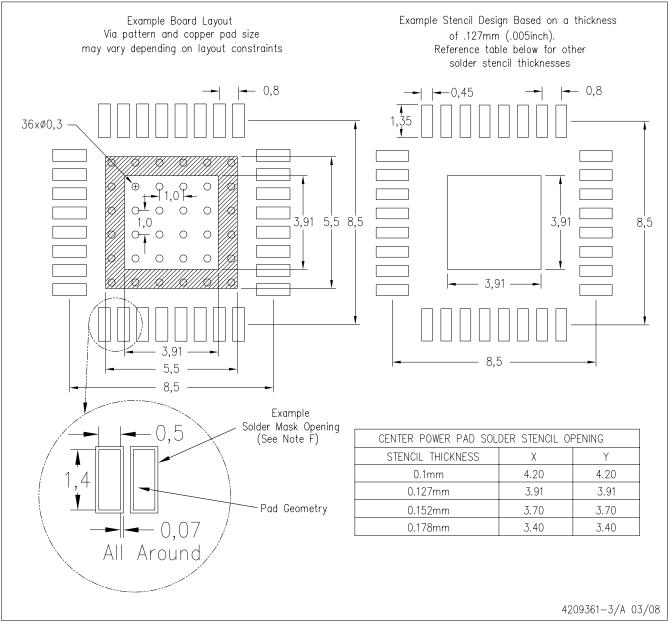
The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: All linear dimensions are in millimeters



VFP (S-PQFP-G32) PowerPAD™



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com https://www.ti.com. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PowerPAD is a trademark of Texas Instruments.



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